August 2001

FDC6331L Integrated Load Switch

General Description

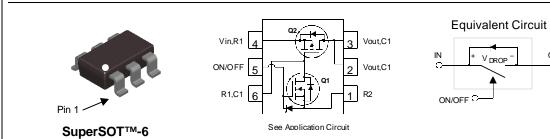
This device is particularly suited for compact power management in portable electronic equipment where 2.5V to 8V input and 2.8A output current capability are needed. This load switch integrates a small N-Channel power MOSFET (Q1) that drives a large PChannel power MOSFET (Q2) in one tiny SuperSOTTM-6 package.

Applications

- Load switch
- Power management

Features

- $\label{eq:linear} \begin{array}{l} \bullet \ -2.8 \ \text{A}, -8 \ \text{V}. \ \ \text{R}_{\text{DS(ON)}} = 55 \ \text{m}\Omega \ \ @ \ \text{V}_{\text{GS}} = -4.5 \ \text{V} \\ \\ \text{R}_{\text{DS(ON)}} = 70 \ \text{m}\Omega \ \ @ \ \text{V}_{\text{GS}} = -2.5 \ \text{V} \\ \\ \text{R}_{\text{DS(ON)}} = 100 \ \text{m}\Omega \ \ @ \ \text{V}_{\text{GS}} = -1.8 \ \text{V} \end{array}$
- Control MOSFET (Q1) includes Zener protection for ESD ruggedness (>6KV Human body model)
- + High performance trench technology for extremely low $R_{\text{DS}(\text{ON})}$



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol		Parameter		Ratings	Units
V _{IN}	Maximum Input	nput Voltage		± 8	V
V _{ON/OFF}	High level ON/0	ON/OFF voltage range		-0.5 to 8	V
Load	Load Current – Continuous (Note 1)		(Note 1)	-2.8	А
		– Pulsed		-9	
PD	Maximum Powe	er Dissipation	(Note 1)	0.7	
		ating and Storage Junction Temperature Range -55 to +150			°C
	al Character	istics	· · ·		
T _J , T _{STG} Therma R _{0JA} R _{0JC}	al Character	0	mbient (Note 1)	180 60	°C/M °C/M
Therma R _{0JA} R _{0JC}	al Character Thermal Resist Thermal Resist	istics ance, Junction-to-Ar ance, Junction-to-C	mbient (Note 1) ase (Note 1)	180	°C/W
Therma R _{θJA} R _{θJC} Packaç	al Character Thermal Resist Thermal Resist	istics ance, Junction-to-Ar ance, Junction-to-C	mbient (Note 1)	180	°C/W

©2001 Fairchild Semiconductor Corporation

OUT

 $^{\circ}$

FDC6331L

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	racteristics					
BVIN	Vin Breakdown Voltage	$V_{\text{ON/OFF}} = 0 \text{ V}, \text{ I}_{\text{D}} = -250 \mu\text{A}$	8			V
Load	Zero Gate Voltage Drain Current	$V_{\text{IN}} = 6.4 \text{ V}, \qquad V_{\text{ON/OFF}} = 0 \text{ V}$			-1	μA
I _{FL}	Leakage Current, Forward	$V_{ON/OFF} = 0 V, V_{IN} = 8 V$			-100	nA
RL	Leakage Current, Reverse	$V_{ON/OFF} = 0 V, V_{IN} = -8 V$			100	nA
On Cha	racteristics (Note 2)					
VON/OFF (th)	Gate Threshold Voltage	$V_{IN} = V_{ON/OFF}, I_D = -250 \ \mu A$	0.4	0.9	1.5	V
R _{DS(on)}	Static Drain–Source On–Resistance (Q2)	$ \begin{array}{ll} V_{\rm IN} = 4.5 \ V, & I_{\rm D} = -2.8 A \\ V_{\rm IN} = 2.5 \ V, & I_{\rm D} = -2.5 \ A \\ \end{array} $		34 45	55 70	mΩ
R _{DS(on)}	Static Drain–Source	$V_{IN} = 1.8 V, \qquad I_D = -2.0 A$ $V_{IN} = 4.5 V, \qquad I_D = 0.4A$		64 3.1	100 4	0
NDS(on)	On–Resistance (Q1)	$V_{IN} = 4.3 V$, $I_D = 0.4 A$ $V_{IN} = 2.7 V$. $I_D = 0.2 A$		3.8	5	Ω

Drain-Source Diode Characteristics and Maximum Ratings

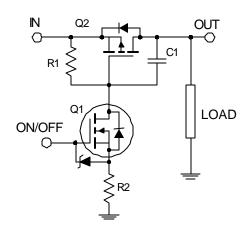
s	Maximum Continuous Drain–Source Diode Forward Current			-0.6	A
V _{SD}	Drain–Source Diode Forward Voltage	$V_{ON/OFF} = 0 V, I_S = -0.6 A$ (Note 2)		-1.2	V

Notes:

 $1.R_{eJA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{eJC} is guaranteed by design while R_{eJA} is determined by the user's board design.

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%.

FDC6331L Load Switch Application Circuit



External Component Recommendation:

For additional in-rush current control, R2 and C1 can be added. For more information, see application note AN1030.

0.4 0.4 V_N = -2.5V V_{IN} = -1.8V -V_{ON/OFF}= -1.5V -8V PW = 300us, D < 2% 0.35 V_{ON/OFF} = -1.5V -8V 0.35 PW = 300us, D < 2% 0.3 125°C 0.3 0.25 0.25 T_J = 125 °C Ξ Ξ -V_{DROP} (' -V DROP 0.2 25 °C 0.2 T_J : 0.15 0.15 25⁰C 0.1 0.1 0.05 0.05 0 0 2 3 5 0 3 5 6 0 1 4 6 1 2 4 -I_L, (A) -I_L, (A) Figure 1. Conduction Voltage Drop Figure 2. Conduction Voltage Drop Variation with Load Current. Variation with Load Current. 0.4 V_N = -4.5V V_{ONOFF} = -1.5V -8V PW = 300us, D ≤ 2% 0.15 $I_{L} = -1A$ 0.35 V_{ON/OFF} = -1.5V -8V ସ୍ତି ^{0.125} 0.3 PW = 300us, D < 2% € ^{0.25} ON-RESISTANCE 0.1 T_J = 125 °C -VDROP (0.2 0.075 0.15 $T_{J} = 125^{O}C$ $T_J = 25^{\circ}C$ 0.05 0.1 $T_{
m J} = 25^{
m O}C$ 0.05 م 0.025 م 0 2 3 4 5 1 6 0 0 -I_L, (A) 1 ² -V_{IN}, INPUT VOLTAGE (V) ⁴ 5 Figure 3. Conduction Voltage Drop Figure 4. On-Resistance Variation With Input Voltage Variation with Load Current. 1 r(t), NORMALIZED EFFECTIVE TRANSIENT THERMAL RESISTANCE $R_{\theta}JA(t) = r(t) + R_{\theta}JA$ + $R_{\theta JA} = 156 \text{ °C/W}$ Ť ŢĦ P(pk) 0.1 $T_J - T_A - P + R_{\theta JA}(t)$ SINGLE PULSE **ŦŦ**₩ Duty Cycle, $D = t_1/t_2$ 02 0.01 0.01 0.0001 0.001 0.01 0.1 1 10 100 1000

FDC6331L

FDC6331L Rev C(W)

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™ Bottomless™ CoolFET™ CROSSVOLT™ DenseTrench™ DOME™ **EcoSPARK™** E²CMOS[™] EnSigna™ FACT™ FACT Quiet Series™ FAST ® FASTr™ FRFET™ GlobalOptoisolator[™] POP[™] GTO™ HiSeC™ ISOPLANAR™ LittleFET™ MicroFET™ MicroPak™ MICROWIRE™

OPTOLOGIC™ OPTOPLANAR™ PACMAN™ Power247™ PowerTrench[®] QFET™ QS™ QT Optoelectronics[™] Quiet Series[™] SILENT SWITCHER®

SMART START™ VCX™ STAR*POWER™ Stealth™ SuperSOT[™]-3 SuperSOT[™]-6 SuperSOT[™]-8 SyncFET™ TinyLogic™ TruTranslation[™] UHC™ UltraFET[®]

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY. FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.
	In Design First Production Full Production